

In the Claims

Please replace claim 43 with the following clean version of the amended in accordance with 37 C.F.R. 1.121(c)(1)(i). Cancel all previous versions of any amended claim.

A marked up version showing amendments to any claims being changed is provided in one or more accompanying pages separate from this amendment in accordance with 37 C.F.R. 1.121(c)(1)(ii). Any claim not accompanied by a marked up version has not been changed relative to the immediate prior version, except that marked up versions are not being supplied for any added claim or canceled claim.

43. (amended) A capacitor forming method comprising:
forming an insulation layer over a substrate, the substrate including an electronic device;
forming an opening into the insulation layer, the opening having a sidewall;
forming a capacitor electrode at least within the opening and over the sidewall;
forming a high K capacitor dielectric layer at least over the capacitor electrode;
after forming the high K capacitor dielectric layer, forming a barrier layer to V_t shift inducing material at least over the insulation layer; and
providing V_t shift inducing material over the barrier layer, the barrier layer retarding movement of the V_t shift inducing material into the electronic device.

Amended
B2